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CMOS Analog Design Using All-Region MOSFET Modeling
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Nonlinear Circuit Simulation and Modeling
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Compact MOSFET Models for VLSI Design
FinFET Modeling for IC Simulation and Design
Transistor Level Modeling for Analog/RF IC Design
Handbook of Digital CMOS Technology, Circuits, and Systems
Industry Standard FDSOI Compact Model BSIM-IMG for IC Design
EDA for IC Implementation, Circuit Design, and Process Technology
Nanoscale Devices
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Structured Analog CMOS Design
State-of-the-Art of Millimeter-Wave Silicon Technology
Strain-Induced Effects in Advanced MOSFETs
Process Variations and Probabilistic Integrated Circuit Design

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Advanced VLSI Design and Testability Issues Springer
Most of the recent texts on compact modeling are limited to a particular class of semiconductor devices and do not provide comprehensive coverage of the field. Having a single comprehensive reference for the compact models of most commonly used semiconductor devices (both active and passive) represents a significant advantage for the reader. Indeed, several kinds of semiconductor devices are routinely encountered in a single IC design or in a single modeling support group. Compact Modeling includes mostly the material that after several years of IC design applications has been found both theoretically sound and practically significant. Assigning the individual chapters to the groups responsible for the definitive work on the subject assures the highest possible degree of expertise on each of the covered models.
Mixed Analog-digital VLSI Devices and Technology Cambridge University Press
Industry Standard FDSOI Compact Model BSIM-IMG for IC Design helps readers develop an understanding of a FDSOI device and its simulation model. It covers the physics and operation of the FDSOI device, explaining not only how FDSOI enables further scaling, but also how it offers unique possibilities in circuits. Following chapters cover the industry standard compact model BSIM-IMG for FDSOI devices. The book addresses core surface-potential calculations and the plethora of real devices and potential effects. Written by the original developers of the industrial standard model, this book is an excellent reference for the new BSIM-IMG compact model for emerging FDSOI technology. The authors include chapters on step-by-step parameters extraction procedure for BSIM-IMG model and rigorous industry grade tests that the BSIM-IMG model has undergone. There is also a chapter on analog and RF circuit design in FDSOI technology using the BSIM-IMG model. Provides a detailed discussion of the BSIM-IMG model and the industry standard simulation model for FDSOI, all presented by the developers of the model Explains the complex operation of the FDSOI device and its use of two independent control inputs Addresses the parameter extraction challenges for those using this model
Mosfet Modeling for Circuit Analysis and Design Springer Nature
Discover the nonlinear methods and tools needed to design real-world microwave circuits with this tutorial guide. Balancing theoretical background with practical tools and applications, it covers everything from the basic properties of nonlinear systems such as gain compression, intermodulation and harmonic distortion, to nonlinear circuit analysis and simulation algorithms, and state-of-the-art equivalent circuit and behavioral modeling techniques. Model formulations discussed in detail include time-domain transistor compact models and frequency-domain linear and nonlinear scattering models. Learn how to apply these tools to designing real circuits with the help of a power amplifier design example, which covers all stages from active device model extraction and the selection of bias and terminations, through to performance verification. Realistic examples, illustrative insights and clearly conveyed mathematical formalism make this an essential learning aid for both professionals working in microwave and RF engineering and graduate students looking for a hands-on guide to microwave circuit design.
Switchmode RF and Microwave Power Amplifiers Springer Science & Business Media
The primary aim of this book is to discuss various aspects of nanoscale device design and their applications including transport mechanism, modeling, and circuit applications. . Provides a platform for modeling and analysis of state-of-the-art devices in nanoscale regime, reviews issues related to optimizing the sub-nanometer device performance and addresses simulation aspect and/or fabrication process of devices Also, includes design problems at the end of each chapter
The Predictive Technology Model in the Late Silicon Era and Beyond Cambridge University Press
This book examines the critical differences between current and next-generation Si technologies (CMOS, BiCMOS and SiC) and technology platforms (e.g. system-on-chip) in mm-wave wireless applications. We provide a basic overview of the two technologies from a technical standpoint, followed by a review of the state-of-the-art of several key building blocks in wireless systems. The influences of system requirements on the choice of semiconductor technology are vital to understanding the merits of CMOS and BiCMOS devices – e.g., output power, battery life, adjacent channel interference, cost restrictions, and so forth. These requirements, in turn, affect component-level design and performance metrics of oscillators, mixers, power and low-noise amplifiers, as well as phase-locked loops and data converters. Finally, the book offers a peek into the next generation of wireless technologies such as THz -band systems and future 6G applications.
Modellierung der Zuverlässigkeit bei Entwurf und Verifikation von Mixed-Signal-Schaltungen CRC Press
This book provides readers with an overview of the design, fabrication, simulation, and reliability of nanoscale semiconductor devices, MEMS, and sensors, as they serve for realizing the next-generation internet of things. The authors focus on how the nanoscale structures interact with the electrical and/or optical performance, how to find optimal solutions to achieve the best outcome, how these apparatus can be designed via models and simulations, how to improve reliability, and what are the possible challenges and roadblocks moving forward.
Compact Models for Integrated Circuit Design Academic Press
Structured Analog CMOS Design describes a structured analog design approach that makes it possible to simplify complex analog design problems and develop a design strategy that can be used for the design of large number of analog cells. It intentionally avoids treating the analog design as a mathematical problem, developing a design procedure based on the understanding of device physics and approximations that give insight into parameter interdependences. The basic design concept consists in analog cell partitioning into the basic analog structures and sizing of these basic analog structures in a predefined procedural design sequence. The procedural design sequence ensures the correct propagation of design specifications, the verification of parameter limits and the local optimization loops. The proposed design procedure is also implemented as a CAD tool that follows this book.

The Physics and Modeling of Mosfets Mosfet Modeling for Circuit Analysis and DesignStrain-Induced Effects in Advanced MOSFETs This book is the first to explain FinFET modeling for IC simulation and the industry standard – BSIM-CMG - describing the rush in demand for advancing the technology from planar to 3D architecture, as now enabled by the approved industry standard. The book gives a strong foundation on the physics and operation of FinFET, details aspects of the BSIM-CMG model such as surface potential, charge and current calculations, and includes a dedicated chapter on parameter extraction procedures, providing a step-by-step approach for the efficient extraction of model parameters. With this book you will learn: Why you should use FinFET The physics and operation of FinFET Details of the FinFET standard model (BSIM-CMG) Parameter extraction in BSIM-CMG FinFET circuit design and simulation Authored by the lead inventor and developer of FinFET, and developers of the BSIM-CM standard model, providing an experts' insight into the specifications of the standard The first book on the industry-standard FinFET model - BSIM-CMG

Multiscale Modelling of Advanced Materials Springer Science & Business Media

This book provides a comprehensive review of the state-of-the-art in the development of new and innovative materials, and of advanced modeling and characterization methods for nanoscale CMOS devices. Leading global industry bodies including the International Technology Roadmap for Semiconductors (ITRS) have created a forecast of performance improvements that will be delivered in the foreseeable future – in the form of a roadmap that will lead to a substantial enlargement in the number of materials, technologies and device architectures used in CMOS devices. This book addresses the field of materials development, which has been the subject of a major research drive aimed at finding new ways to enhance the performance of semiconductor technologies. It covers three areas that will each have a dramatic impact on the development of future CMOS devices: global and local strained and alternative materials for high speed channels on bulk substrate and insulator; very low access resistance; and various high dielectric constant gate stacks for power scaling. The book also provides information on the most appropriate modeling and simulation methods for electrical properties of advanced MOSFETs, including ballistic transport, gate leakage, atomistic simulation, and compact models for single and multi-gate devices, nanowire and carbon-based FETs. Finally, the book presents an in-depth investigation of the main nanocharacterization techniques that can be used for an accurate determination of transport parameters, interface defects, channel strain as well as RF properties, including capacitance-conductance, improved split C-V, magnetoresistance, charge pumping, low frequency noise, and Raman spectroscopy.

Compact Modeling World Scientific

This book constitutes the refereed post-conference proceedings of the 9th International Conference on Broadband Communications, Networks, and Systems, Broadnets 2018, which took place in Faro, Portugal, in September 2018. The 30 revised full and 16 workshop papers were carefully reviewed and selected from 68 submissions. The papers are thematically grouped as follows: Advanced Techniques for IoT and WSNs; SDN and Network Virtualization; eHealth and Telemedicine Mobile Applications; Security and Privacy Preservation; Communication Reliability and Protocols; Spatial Modulation Techniques; Hardware Implementation and Antenna Design.

Predictive Technology Model for Robust Nanoelectronic Design Springer

Semiconductor technologies continue to evolve and amaze us. New materials, new structures, new manufacturing tools, and new advancements in modelling and simulation form a breeding ground for novel high performance electronic and photonic devices. This book covers all aspects of semiconductor technology concerning materials, technological processes, and devices, including their modelling, design, integration, and manufacturing.

ESD Protection Device and Circuit Design for Advanced CMOS Technologies Academic Press

This book facilitates the VLSI-interested individuals with not only in-depth knowledge, but also the broad aspects of it by explaining its applications in different fields, including image processing and biomedical. The deep understanding of basic concepts gives you the power to develop a new application aspect, which is very well taken care of in this book by using simple language in explaining the concepts. In the VLSI world, the importance of hardware description languages cannot be ignored, as the designing of such dense and complex circuits is not possible without them. Both Verilog and VHDL languages are used here for designing. The current needs of high-performance integrated circuits (ICs) including low power devices and new emerging materials, which can play a very important role in achieving new functionalities, are the most interesting part of the book. The testing of VLSI circuits becomes more crucial than the designing of the circuits in this nanometer technology era. The role of fault simulation algorithms is very well explained, and its implementation using Verilog is the key aspect of this book. This book is well organized into 20 chapters. Chapter 1 emphasizes on uses of FPGA on various image processing and biomedical applications. Then, the descriptions enlighten the basic understanding of digital design from the perspective of HDL in Chapters 2–5. The performance enhancement with alternate material or geometry for silicon-based FET designs is focused in Chapters 6 and 7. Chapters 8 and 9 describe the study of bimolecular interactions with biosensing FETs. Chapters 10–13 deal with advanced FET structures available in various shapes, materials such as nanowire, HFET, and their comparison in terms of device performance metrics calculation. Chapters 14–18 describe different application-specific VLSI design techniques and challenges for analog and digital circuit designs. Chapter 19 explains the VLSI testability issues with the description of simulation and its categorization into logic and fault simulation for test pattern generation using Verilog HDL. Chapter 20 deals with a secured VLSI design with hardware obfuscation by hiding the IC's structure and function, which makes it much more difficult to reverse engineer.

CRC Press

Predictive Technology Model for Robust Nanoelectronic Design explains many of the technical mysteries behind the Predictive Technology Model (PTM) that has been adopted worldwide in explorative design research. Through physical derivation and technology extrapolation, PTM is the de-factor device model used in electronic design. This work explains the systematic model development and provides a guide to robust design practice in the presence of variability and reliability issues. Having interacted with multiple leading semiconductor companies and university research teams, the author brings a state-of-the-art perspective on technology scaling to this work and shares insights gained in the practices of device modeling.

Broadband Communications, Networks, and Systems Cambridge University Press

This book provides a comprehensive reference for everything that has to do with digital circuits. The author focuses equally on all levels of abstraction. He tells a bottom-up story from the physics level to the finished product level. The aim is to provide a full account of the experience of designing, fabricating, understanding, and testing a microchip. The content is structured to be very accessible and self-contained, allowing readers with diverse backgrounds to read as much or as little of the book as needed. Beyond a basic foundation of mathematics and physics, the book makes no assumptions about prior knowledge. This allows someone new to the field to read the book from the beginning. It also means that someone using the book as a reference will be able to answer their questions without referring to any external sources.

BSIM4 and MOSFET Modeling for IC Simulation Springer Science & Business Media

One of the first books to cover advanced silicon-based technologies, Advanced Silicon and Semiconducting Silicon Alloy-Based Materials and Devices presents important directions for research into silicon, its alloy-based semiconducting devices, and its development in commercial applications. The first section deals with single/mono crystalline silicon, focusing on the effects of heavy doping; the structure and electronic properties of defects and their impact on devices; the MBE of silicon, silicon alloys, and metals; CVD techniques for silicon and silicon germanium; the material properties of silicon germanium strained layers; silicon germanium heterojunction bipolar applications; FETs, IR detectors, and resonant tunneling devices in silicon, silicon germanium, and d-doped silicon; and the fascinating properties of crystalline silicon carbide and its applications. The second section explores polycrystalline silicon. It examines large grain polysilicon substrates for solar cells; the properties, analysis, and modeling of polysilicon TFTs; the technology of polysilicon TFTs in LCD displays; and the use of polycrystalline silicon and its alloys in VLSI applications. With contributors from leading academic and industrial research centers, this book provides wide coverage of fabrication techniques, material properties, and device applications.

Outlook and Challenges of Nano Devices, Sensors, and MEMS Springer Nature

Compact Models for Integrated Circuit Design: Conventional Transistors and Beyond provides a modern treatise on compact models for circuit computer-aided design (CAD). Written by an author with more than 25 years of industry experience in semiconductor processes, devices, and circuit CAD, and more than 10 years of academic experience in teaching compact modeling courses, this first-of-its-kind book on compact SPICE models for very-large-scale-integrated (VLSI) chip design offers a balanced presentation of compact modeling crucial for addressing current modeling challenges and understanding new models for emerging devices. Starting from basic semiconductor physics and covering state-of-the-art device regimes from conventional micron to nanometer, this text: Presents industry standard models for bipolar-junction transistors (BJTs), metal-oxide-semiconductor (MOS) field-effect-transistors (FETs), FinFETs, and tunnel field-effect transistors (TFETs), along with statistical MOS models Discusses the major issue of process variability, which severely impacts device and circuit performance in advanced technologies and requires statistical compact models Promotes further research of the evolution and development of compact models for VLSI circuit design and analysis Supplies fundamental and practical knowledge necessary for efficient integrated circuit (IC) design using nanoscale devices Includes exercise problems at the end of each chapter and extensive references at the end of the book Compact Models for Integrated Circuit Design: Conventional Transistors and Beyond is intended for senior undergraduate and graduate courses in electrical and electronics engineering as well as for researchers and practitioners working in the area of electron devices. However, even those unfamiliar with semiconductor physics gain a solid grasp of compact modeling concepts from this book.

Semiconductor Technologies Springer Nature

Practicing designers, students, and educators in the semiconductor field face an ever expanding portfolio of MOSFET models. In Compact MOSFET Models for VLSI Design , A.B. Bhattacharyya presents a unified perspective on the topic, allowing the practitioner to view and interpret device phenomena concurrently using different modeling strategies. Readers will learn to link device physics with model parameters, helping to close the gap between device understanding and its use for optimal circuit performance. Bhattacharyya also lays bare the core physical concepts that will drive the future of VLSI development, allowing readers to stay ahead of the curve, despite the relentless evolution of new models. Adopts a unified approach to guide students through the confusing array of MOSFET models Links MOS physics to device models to prepare practitioners for real-world design activities Helps fabless designers bridge the gap with off-site foundries Features rich coverage of: quantum mechanical related phenomena Si-Ge strained-Silicon substrate non-classical structures such as Double Gate MOSFETs Presents topics that will prepare readers for long-term developments in the field Includes solutions in every chapter Can be tailored for use among students and professionals of many levels Comes with MATLAB code downloads for independent practice and advanced study This book is essential for students specializing in VLSI Design and indispensible for design professionals in the microelectronics and VLSI industries. Written to serve a number of experience levels, it can be used either as a course textbook or practitioner’s reference. Access the MATLAB code, solution manual, and lecture materials at the companion website: www.wiley.com/go/bhattacharyya

MOSFET Modeling & BSIM3 User’s Guide Woodhead Publishing

This volume provides a timely description of the latest compact MOS transistor models for circuit simulation. The first generation BSIM3 and BSIM4 models that have dominated circuit simulation in the last decade are no longer capable of characterizing all the important features of modern sub-100nm MOS transistors. This book discusses the second generation MOS transistor models that are now in urgent demand and being brought into the initial phase of manufacturing applications. It considers how the models are to include the complete drift-diffusion theory using the surface potential variable in the MOS transistor channel in order to give one characterization equation.

Advanced Silicon & Semiconducting Silicon-Alloy Based Materials & Devices Springer Science & Business Media

Mosfet Modeling for Circuit Analysis and DesignStrain-Induced Effects in Advanced MOSFETsSpringer Science & Business Media

Nanoscale CMOS John Wiley & Sons

ESD Protection Device and Circuit Design for Advanced CMOS Technologies is intended for practicing engineers working in the areas of circuit design, VLSI reliability and testing domains. As the problems associated with ESD failures and yield losses become significant in the modern semiconductor industry, the demand for

graduates with a basic knowledge of ESD is also increasing. Today, there is a significant demand to educate the circuits design and reliability teams on ESD issues. This book makes an attempt to address the ESD design and implementation in a systematic manner. A design procedure involving device simulators as well as circuit simulator is employed to optimize device and circuit parameters for optimal ESD as well as circuit performance. This methodology, described in ESD Protection Device and Circuit Design for Advanced CMOS Technologies has resulted in several successful ESD circuit design with excellent silicon results and demonstrates its strengths.